

Number	Hits	Search Text	DB	Time stamp
9	5	((ingan gainn) adj channel)	USPAT; US-PCPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/17 1:44
10	19	((ingan gainn) (indium adj gallium adj nitride) adj channel)	USPAT; US-PCPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/17 1:44
11	36	((hemt (high adj electron adj mobility adj transistor)) and ((gan (gallium adj nitride)) and relax94	USPAT; US-PCPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/17 1:44
12	18	((hemt (high adj electron adj mobility adj transistor)) and ((gan (gallium adj nitride)) and relax94) and ((ingan gainn (indium adj gallium adj nitride))	USPAT; US-PCPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/17 1:44

Number	Hits	Search Text	IB	Time Stamp
14	2	((lingan gainn; near5 channel; and partial\$2 adj relaxed;	USPAT; US-POHUB; EIO; JIO; DEWENT; IBM TOR	1997/07/11 11:11
15	1	(hemt (high adj electron adj mobility adj transistor)) and ((partial; near5 relaxed; adj channel;	USPAT; US-POHUB; EIO; JIO; DEWENT; IBM TOR	1997/07/11 11:11
16	1	(hemt (high adj electron adj mobility adj transistor; and third near5 channel; and @ay<100) and ((lingan gainn; and ((partial\$2 adj relaxed; near5 channel;	USPAT; US-POHUB; EIO; JIO; DEWENT; IBM TOR	1997/07/11 11:11
17	0	((partial\$2 adj relaxed; near5 channel; and ((lingan gainn;	USPAT; US-POHUB; EIO; JIO; DEWENT; IBM TOR	1997/07/11 11:11
18	17	((lingan gainn; near5 channel;	USPAT; US-POHUB; EIO; JIO; DEWENT; IBM TOR	1997/07/11 11:11
19	3	(hemt (high adj electron adj mobility adj transistor)) and ((lingan gainn; near5 channel;	USPAT; US-POHUB; EIO; JIO; DEWENT; IBM TOR	1997/07/11 11:11